









# **CEB3112**

## 30V Δ 9mΩ Δ 46A Δ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

TO263 (D2PAK) package ▲ MSL 3

Super high dense cell density for extremely low R<sub>DS(ON)</sub>

High power and current handling capability

# **MAXIMUM RATINGS**

Parameter (T <sub>c</sub> = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	30V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current at T <sub>C</sub> = 25°C	<b>I</b> D	46A
Continuous Drain Current at T <sub>C</sub> = 100°C	I <sub>D</sub>	32A
Pulsed Drain Current Note 1	I <sub>DM</sub> Note 5	184A
Maximum Power Dissipation at T <sub>C</sub> = 25°C	P <sub>D</sub>	45W
Power Dissipation Derating above 25°C	$\Delta P_D$	0.3W/°C
Single Pulsed Avalanche Energy Note 6	E <sub>AS</sub>	50mJ
Single Pulsed Avalanche Current Note 6	I <sub>AS</sub>	10A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +175°C

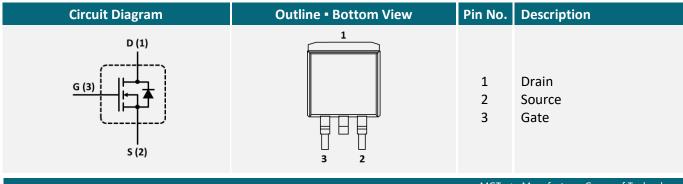
## THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	3.3°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>TH JA</sub>	62.5°C/W

# **APPLICATIONS**

<b>Battery Management</b>	DC/DC	High Side	Low Side	Power
Systems	Converter	Switches	Switches	Banks
+4-				4

# **PIN DESCRIPTION**





# **ELECTRICAL CHARACTERISTICS** ▲ T<sub>C</sub> = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_{D} = 250\mu A$	$BV_{DSS}$	30			V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	$I_{GSSR}$			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	$V_{GS(th)}$	1		3	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 20A$	R <sub>DS(ON)</sub>		9	12	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 4.5V$ , $I_D = 10A$	R <sub>DS(ON)</sub>		11	14	mΩ
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	C <sub>ISS</sub>		735		pF
Output Capacitance	$V_{DS} = 15V$ , $V_{GS} = 0V$ , $f = 1MHz$	Coss		145		pF
Reverse Transfer Capacitance	$V_{DS} = 15V$ , $V_{GS} = 0V$ , $f = 1MHz$	C <sub>RSS</sub>		110		pF
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{DD} = 15V$ , $V_{GS} = 10V$ , $I_D = 10A$ , $R_{G(ext)} = 3\Omega$	t <sub>D(ON)</sub>		13		ns
Turn-On Rise Time	$V_{DD} = 15V$ , $V_{GS} = 10V$ , $I_{D} = 10A$ , $R_{G(ext)} = 3\Omega$	t <sub>R</sub>		7		ns
Turn-Off Delay Time	$V_{DD} = 15V$ , $V_{GS} = 10V$ , $I_D = 10A$ , $R_{G(ext)} = 3\Omega$	t <sub>D(OFF)</sub>		45		ns
Turn-Off Fall Time	$V_{DD}$ = 15V, $V_{GS}$ = 10V, $I_{D}$ = 10A, $R_{G(ext)}$ = 3 $\Omega$	t <sub>F</sub>		18		ns
Total Gate Charge	$V_{DS} = 15V$ , $V_{GS} = 4.5V$ , $I_{D} = 10A$	$Q_{G}$		9.3		nC
Gate Source Charge	$V_{DS} = 15V$ , $V_{GS} = 4.5V$ , $I_{D} = 10A$	$Q_{GS}$		1.8		nC
Gate Drain Charge	$V_{DS} = 15V$ , $V_{GS} = 4.5V$ , $I_{D} = 10A$	$Q_{GD}$		4.8		nC
<b>Drain-Source Diode Characteristics a</b>	nd Maximum Ratings					
Drain-Source Diode Forward Current		I <sub>S</sub>			34	А
Drain-Source Diode Forward Voltage Note 2	$V_{GS}$ = 0V, $I_S$ = 1A	$V_{SD}$			1.3	V

# Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: Limited only by maximum temperature allowed.
- 5: Pulse width limited by safe operating area.
- 6: L = 1mH,  $I_{AS}$  = 10A,  $V_{DD}$  = 25V,  $R_G$  = 25Ω, Starting  $T_J$  = 25°C.



## REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



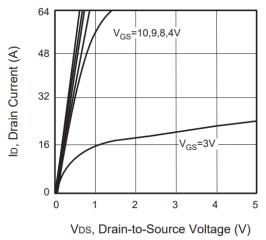


Fig. 2 • Transfer Characteristics

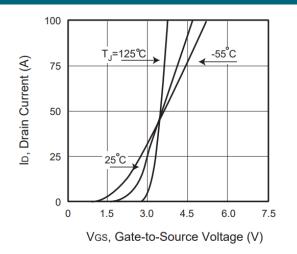


Fig. 3 • Capacitance

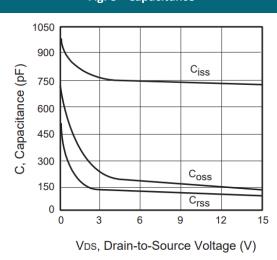


Fig. 4 • On-Resistance Variation with Temperature

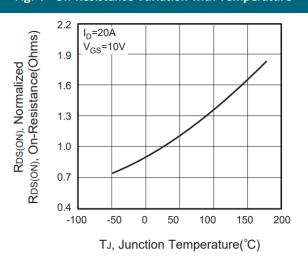


Fig. 5 • Gate Threshold Variation with Temperature

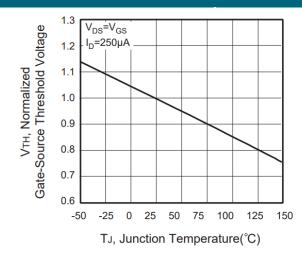
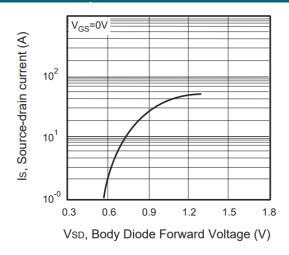


Fig. 6 • Body Diode Forward Voltage Variation with Source Current





## REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

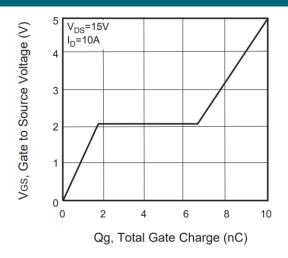


Fig. 8 • Maximum Safe Operating Area

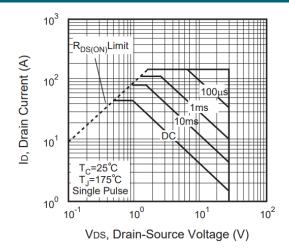


Fig. 9 • Breakdown Voltage Variation vs. Temperature

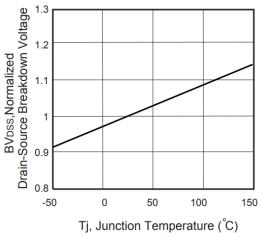


Fig. 10 • Switching Test Circuit

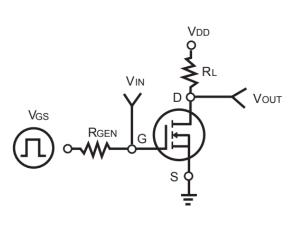
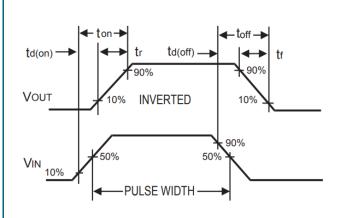


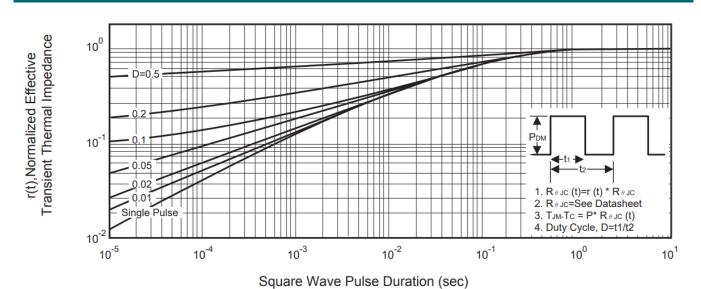
Fig. 11 • Switching Waveforms



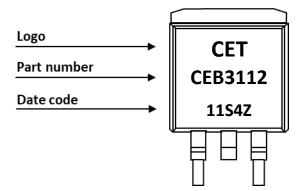


## REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



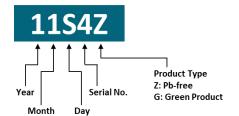


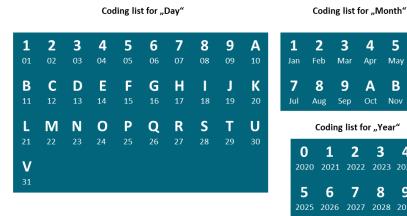
## **PART MARKING**



#### **DATE CODE**

Example: 11S4Z





4 5 6

Apr May

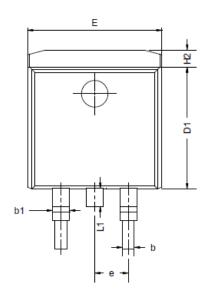
A В C

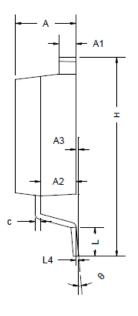
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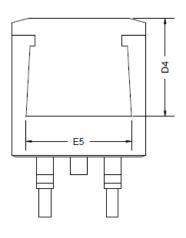
7 8 9

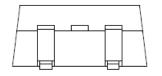


# **PACKAGE OUTLINE**









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0.00	0.13	0.25
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
С	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	-	-

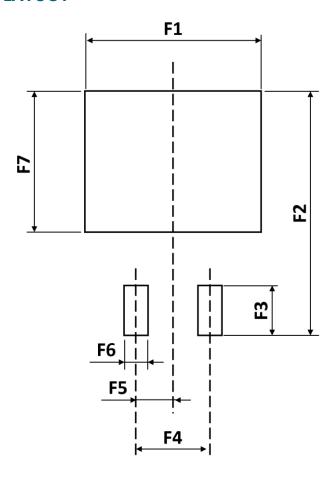
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)			
Е	9.86	10.16	10.36			
E5	7.06	-	-			
е	2.54 BSC					
Н	14.70 15.10		15.50			
H2	1.07 1.27		1.47			
L	2.00	2.30	2.60			
L1	1.40	1.55	1.70			
L4	0.25 BSC					
θ	0°	5°	9°			

# **ORDERING INFORMATION**

Part Number	Package	Packing Reel Qty.		Inner Box Qty.	Outer Box Qty.
CEB3112	TO263 (D2PAK)	Reel	800pcs	800pcs	6,400pcs



# **RECOMMENDED PAD LAYOUT**



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	12.20	-
F2	-	16.90	-
F3	-	2.54	-
F4	-	5.08	-

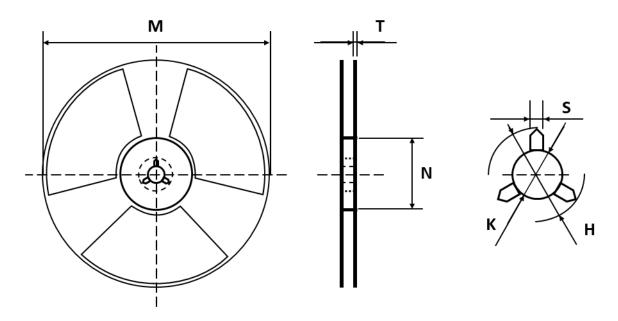
Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
-	2.54	-
-	1.60	-
-	9.75	-
	(Min.) - -	- 2.54 - 1.60

## Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

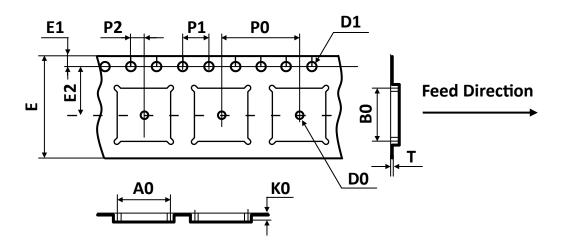


# **REEL DIMENSIONS** ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	H	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	Ø330	+2.00	+0 50	+0.20	+0.50	+0.50	+0.50
		±2.00	±2.00 ±0.50	±0.20	±0.50	-0.20	-0.20

# **TAPE DIMENSIONS** ▲ All dimensions in mm

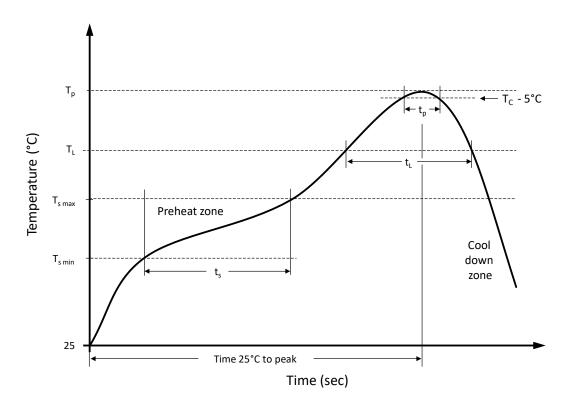


Package	Α0	В0	КО	D0	D1	E	E1	E2	P0	P1	P2	Т
TO263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D <sup>2</sup> PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



# RECOMMENDED REFLOW SOLDERING PROFILE



# **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T <sub>s max</sub>	150 °C	200 °C
Preheat time t <sub>s</sub> from T <sub>s min</sub> to T <sub>s max</sub>	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	$T_L$	183 °C	217 °C
Time t <sub>L</sub> maintained above T <sub>L</sub>	t <sub>L</sub>	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t <sub>p</sub>	20 seconds max.	30 seconds max.
Ramp-down rate (T <sub>L</sub> to T <sub>p</sub> )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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